

Claims

1. A manufacturing method of a display device characterized by including a step of forming a wiring by
5 partially forming a conductor film over a substrate by use of plasma treatment means having an electrode for generating plasma at a pressure of 5 to 800 Torr.

2. A manufacturing method of a display device characterized by including a step of forming a wiring by
10 partially forming a conductor film over a substrate by use of plasma treatment means having a plurality of electrodes for generating plasma at a pressure of 5 to 800 Torr.

3. A manufacturing method of a display device characterized by comprising steps of:
15 partially forming a conductor film over a substrate at a pressure of 5 to 800 Torr by use of first plasma treatment means;

forming a resist mask on the conductor film; and
partially etching the conductor film at a pressure of
20 5 to 800 Torr by use of second plasma treatment means with the resist mask as a mask, and forming a wiring.

4. A manufacturing method of a display device characterized by comprising steps of:
partially forming a conductor film over a substrate
25 at a pressure of 5 to 800 Torr by use of first plasma treatment

means having a plurality of electrodes;

forming a resist mask on the conductor film; and

partially etching the conductor film at a pressure of
5 to 800 Torr by use of second plasma treatment means with
5 the resist mask as a mask and forming a wiring.

5. A manufacturing method of a display device
characterized by comprising steps of:

partially forming a conductor film over a substrate
at a pressure of 5 to 800 Torr by use of first plasma treatment
10 means;

forming a resist mask on the conductor film; and

partially etching the conductor film at a pressure of
5 to 800 Torr by use of second plasma treatment means having
a plurality of electrodes with the resist mask as a mask and
15 forming a wiring.

6. The manufacturing method of the display device
according to any of claims 1 to 5, wherein the substrate has
a size of 1,000 x 1,200 mm² or more.

7. The manufacturing method of the display device
20 according to any of claims 1 to 5, wherein the plasma treatment
means scans the substrate in one direction.

8. The manufacturing method of the display device
according to any of claims 1 to 5, wherein the plasma treatment
means alternately scans the substrate in a row direction and
25 in a column direction.

9. The manufacturing method of the display device according to any of claims 1 to 5, wherein the resist mask is formed by use of liquid droplet jetting means.

10. A manufacturing method of a display device
5 characterized by comprising steps of:

forming an insulating film covering a thin film transistor; and

partially blowing a reactive gas to the insulating film and forming an open portion.

10 11. A manufacturing method of a display device characterized by comprising steps of:

forming an insulating film covering a thin film transistor;

forming a resist mask on the insulating film; and
15 etching the insulating film by using the resist mask as a mask;

wherein the resist mask is formed by photo-lithographically processing a resist film partially formed by liquid droplet jetting means; and

20 wherein etching of the insulating film includes a step of conducting etching by use of plasma treatment means at a pressure of 5 to 800 Torr.